



2871

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT Application of)
Yasuhiko TAKEMURA) Art Unit: 2871 6-14-01
Serial No.: 09/342,235) Examiner: Unassigned T. Flowers
Filed: June 29, 1999)
For: SEMICONDUCTOR DEVICE HAVING AT LEAST)
FIRST AND SECOND THIN FILM TRANSISTORS)

CERTIFICATE OF MAILING
I hereby certify that this correspondence is being
deposited with the United States Postal Service with
sufficient postage as First Class Mail in an envelope
addressed to: Commissioner for Patents, Washington,
D.C. 20231, on June 4, 2001.

Maynard L. Hammel

SUPPLEMENTAL AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:

Please amend the above-identified application as follows:

IN THE TITLE:

Please amend the title as follows:

--SEMICONDUCTOR DEVICE HAVING AT LEAST FIRST AND SECOND THIN FILM TRANSISTORS--

IN THE ABSTRACT:

--A semiconductor device having a substrate having an insulating surface; at least first and second semiconductor islands formed over the substrate where each of the semiconductor islands has a channel region and a pair of impurity regions; an insulating film formed over the substrate, the insulating film including at least first and second gate insulating films formed over the first and second semiconductor islands, respectively; at least first and second gate electrodes formed over the first and second semiconductor islands with the first and second gate insulating films interposed therebetween; a wiring formed on the insulating film for electrically connecting one of the impurity regions of the first semiconductor island with the

RECEIVED
JUN 11 2001
TC 2000 MAIL ROOM

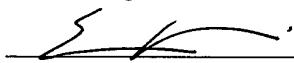
Application No. 09/342,235
Art Unit: 2871

Docket No. 0756-1986
Page 2

second gate electrode where said wiring is connected to the one of the impurity regions through a hold opened in the insulating film; an interlayer insulating film formed over the first and second semiconductor islands, the first and second gate electrodes and the wiring; and a pixel electrode formed over the interlayer insulating film electrically connected to one of the pair of the impurity regions of the second semiconductor island.--

cont
B1
Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact Applicant's undersigned attorney at the telephone number listed below.

Respectfully submitted,


Eric J. Robinson
Reg. No. 38,285

NIXON PEABODY LLP
8180 Greensboro Drive, Suite 800
McLean, Virginia 22102
(703) 790-9110